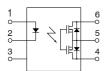


6.3 .248 .248 .248 .083

mm inch



FEATURES

1. 1 channel (Form B) in super miniature design

The device comes in a super-miniature SO package measuring (W) $4.4 \times$ (L) $6.3 \times$ (H) 2.1 mm (W) .173× (L) .248×(H) .083 inch —approx. 25% of the volume and 50% of the footprint size of DIP type PhotoMOS Relays.

TYPES

Output rating* Part No. Packing guantity Package Type I oad Load size Tube packing style Tape and reel packing style Tube Tape and reel voltage current 1 tube contains: AQV414SX AQV414SZ AC/DC 75 pcs. 400V 100mA SOP6pin AQV414S (Picked from the (Picked from the 1,000 pcs. 1 batch contains: type 1/2/3-pin side) 4/5/6-pin side) 1,500 pcs.

* Indicate the peak AC and DC values.

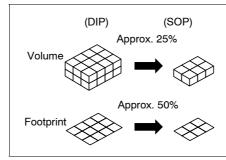
Note: For space reasons, the initial letters of the part number "AQ" the package style indicator "X" or "Z" are not marked on the relay. (Ex. the label for product number AQV414S is V414S)

RATING

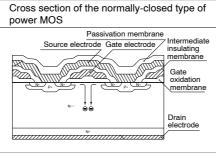
1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

ltem		Symbol	Type of connection	AQV414S	Remarks	
Input	LED forward current	IF		50 mA		
	LED reverse voltage	VR		5 V		
	Peak forward current	FP		1 A	f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	Pin		75 mW		
Output	Load voltage (peak AC)	VL		400 V		
	Continuous load current	١L	A	0.10 A		
			В	0.11 A	A connection: Peak AC, DC B,C connection: DC	
			С	0.12 A	B,C connection. DC	
	Peak load current	peak		0.3 A	A connection: 100 ms (1 shot) VL= DC	
	Power dissipation	Pout		450 mW		
Total power dissipation		Ρτ		500 mW		
I/O isolation voltage		Viso		1,500 V AC		
Temperature limits	Operating	Topr		-40°C to +85°C -40°F to +185°F	Non-condensing at low temperatures	
	Storage		Tstg	-40°C to +100°C -40°F to +212°F		

GU (General Use) Type SOP Series [1-Channel (Form B) Type]



2. Low on resistance (Max. 50 Ω) at 400 V for normally-closed type has been achieved thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-Diffused and Selective Doping) method.



GU PhotoMOS (AQV414S)

c **FL**°us

3. Tape and reel

The device comes standard in a tape and reel (1,000 pcs./reel) to facilitate automatic insertion machines.

4. Controls low-level analog signals PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. Low-level off state leakage current

In contrast to the SSR with an off state leakage current of several milliamperes, the PhotoMOS relay features a very small off state leakage current of typ. 100 pA even at the rated load voltage of 400 V.

6. Low thermal electromotive force (Approx. 1 $\mu\text{V})$

TYPICAL APPLICATIONS

- Telephones
 - Measuring instruments
 - Computer
 - Industrial robots
 - High-speed inspection machines

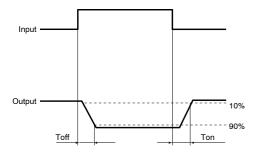
GU PhotoMOS (AQV414S)

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item				Type of connec- tion	AQV414S	Remarks
Input	LED operate (OFF) current	Typical	Foff		0.6 mA	l∟= Max.
		Maximum			3 mA	
	LED reverse (ON) current	Minimum	1-		0.4 mA	l∟= Max.
		Typical	Fon		0.55 mA	
		Typical	VF		1.25 V (1.14 V at I⊧ = 5 mA)	I⊧= 50 mA
	LED dropout voltage	Maximum	VF		1.5 V	
Output	On resistance	Typical	Ron		26 Ω	I⊧= 0 mA I∟= Max. Within 1 s on time
		Maximum		A	50 Ω	
		Typical	Ron		20 Ω	I⊧ = 0 mA I∟ = Max. Within 1 s on time
		Maximum		В	25 Ω	
		Typical			10 Ω	I⊧ = 0 mA I∟ = Max. Within 1 s on time
		Maximum	Ron	С	12.5 Ω	
	Off state leakage current	Maximum	Leak	_	1 µA	I⊧ = 5 mA V∟ = Max.
Transfer characteristics		Typical	-		0.47 ms	I⊧= 0 mA > 5 mA V∟ = Max.
	Operate (OFF) time*	Maximum	Toff	_	1.0 ms	
	Deverse (ON) time*	Typical	-		0.28 ms	I⊧= 5 mA > 0 mA V∟ = Max.
	Reverse (ON) time*	Maximum	Ton	_	1.0 ms	
	1/O conscitones	Typical	0		0.8 pF	f = 1 МНz Vв = 0 V
	I/O capacitance	Maximum	Ciso	_	1.5 pF	
	Initial I/C isolation resistance	Minimum	Riso		1,000 MΩ	500 V DC

Note: Recommendable LED forward current $I_F = 5mA$.

*Operate/Reverse time

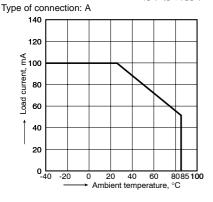


Dimensions Schematic and Wiring Diagrams Cautions for Use

REFERENCE DATA

1. Load current vs. ambient temperature characteristics

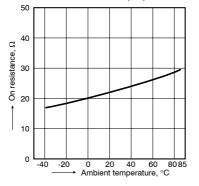
Allowable ambient temperature: -40°C to +85°C -40°F to +185°F



2. On resistance vs. ambient temperature characteristics

characteristics Measured portion: between terminals 4 and 6;

LED current: 0 mA; Continuous load current: 100 mA (DC)

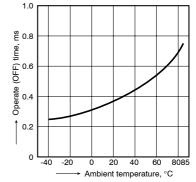


3. Operate (OFF) time vs. ambient temperature

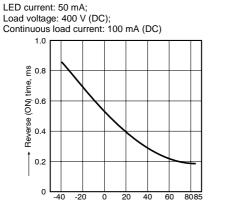
characteristics LED current: 5 mA;

Load voltage: 400 V (DC);

Continuous load current: 100 mA (DC)



Type of connection

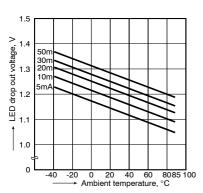


Ambient temperature, °C

4. Reverse (ON) time vs. ambient temperature

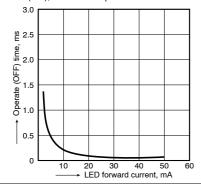
characteristics

7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



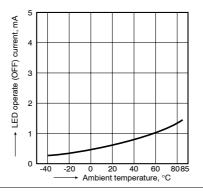
10. Operate (OFF) time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



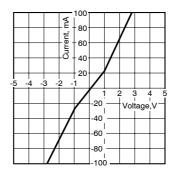
5. LED operate (OFF) current vs. ambient temperature characteristics Load voltage: 400 V (DC);

Continuous load current: 100 mA (DC)



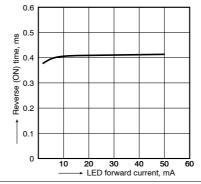
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



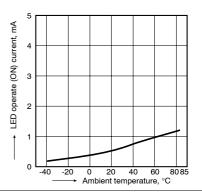
11. Reverse (ON) time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



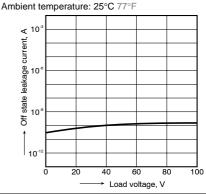
GU PhotoMOS (AQV414S)

6. LED reverse (ON) current vs. ambient temperature characteristics Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 4 and 6; LED current: 5 mA;



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6; Frequency: 1 MHz;

